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IAP9 Rec'd PCT/PTO 06 APR 2006

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

SAKAI et al

International Appln. No.: PCT/JP2004/014603

Filed: Concurrently herewith

Attorney Dkt. No.: 60562.00009

For: SEMICONDUCTOR SUBSTRATE, SEMICONDUCTOR DEVICE AND
PROCESS FOR PRODUCING SEMICONDUCTOR SUBSTRATE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
Attention: PCT DO/EO/US

April 6, 2006

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R.1.97(b).

The references cited in the attached Form PTO-1449 were cited in the enclosed International Search Report issued by the Japanese Patent Office in connection with the above international application. It is understood that the Japanese Patent Office has sent a copy of each of the cited references to the U.S. Patent and Trademark Office. However, for the Examiner's convenience, a copy of each cited reference other than U.S. patents or U.S. patent publications are attached hereto. Please note that U.S. Patent Publication No. 2003/0141504 cited in the attached PTO-1449 corresponds to Japanese Patent Publication No. 2003-152191 cited in the attached

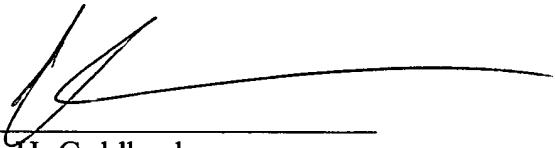
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International Search Report. Also submitted herewith is a reference cited by the applicants.

In view of the above, all requirements of 37 CFR 1.97 and all official guidelines pertaining to Information Disclosure Statements have been complied with, and it is therefore respectfully requested that the Examiner consider the references and make them of record in this application.

In the event that there are any fees due with respect to the filing of this paper, please charge Counsel's Deposit Account No. 50-2222.

Respectfully submitted,



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Enclosures: PTO-1449 Form
International Search Report
References (8)

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FORM PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 60562.00009	SERIAL NO. New Application
LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>				APPLICANT SAKAI et al	
				FILING DATE April 6, 2006	GROUP Not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	AA	2003/0141504	07/31/03	Kuwabara et al			
	AB						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO PART.
	AC	2003-152191	05/23/2003	Japan			
	AD	2001-102442	04/13/2001	Japan			xx
	AE	2000-150664	05/30/2000	Japan			xx
	AF	10-209453	08/07/1998	Japan			xx
	AG	2004-349702	12/09/2004	Japan			xx
	AH	07-335735	12/22/1995	Japan			xx
	AI	05-021465	01/29/1993	Japan			xx

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	AJ	Sasaki et al, "Proposal of a Multi-Layer Channel MOSFET: the application of selective etching for Si/SiGe stacked layers," Applied Surface Science, Vol. 234, pp 270-273.
	AK	
	AL	

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.